

WAFER PROCESSING METHOD

ABSTRACT OF THE DISCLOSURE

Disclosed herein is a wafer processing method including a processed position measuring step of imaging an area including a beam plasma generated by applying a pulsed laser beam to a wafer, by using an imaging unit during the formation of a laser processed groove on the wafer, and next measuring the positional relation between the position of the beam plasma and a preset processing position. Accordingly, it is possible to check whether or not the laser processed groove is formed at a desired position, in real time during laser processing. If the position of the laser processed groove is deviated, the processed position can be immediately corrected.

Figure 8